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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Info Patent Application of: Leonard Forbes et al.

Title: OPERATING A MEMORY DEVICE

Attorney Docket No.: 303.356US4

Customer No.: 21186

PATENT APPLICATION TRANSMITTAL

MAIL STOP PATENT APPLICATION

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

We are transmitting herewith the following attached items and information (as indicated with an "X"):

Return postcard.

CONTINUATION of prior Patent Application No.(08/902133) (under 37 CFR 1.53(b)) comprising:

Specification (40 pgs, including claims numbered 1 through 59 and a 1 page Abstract).

Formal Drawing(s) (7 sheets).

Copy of signed Combined Declaration and Power of Attorney (6 pgs) from prior application.

Incorporation by Reference: *The entire disclosure of the prior application, from which a copy of the oath or declaration is supplied herewith, is considered as being part of the disclosure of the accompanying application and is hereby incorporated by reference therein.*

Check in the amount of \$1816.00 to pay the filing fee.

Prior application is assigned of record to Micron Technology, Inc..

Information Disclosure Statement (1 pgs), Form 1449 (11 pgs) References NOT enclosed, cited in prior application.

Communication Concerning Related Applications (3 pgs.).

The filing fee has been calculated below as follows:

	No. Filed	No. Extra	Rate	Fee
TOTAL CLAIMS	59-20	39	x 18.00 =	\$702.00
INDEPENDENT CLAIMS	7-3	4	x 86.00 =	\$344.00
[] MULTIPLE DEPENDENT CLAIMS PRESENTED				\$0.00
BASIC FEE				\$770.00
TOTAL				\$1816.00

Please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

Customer Number: 21186

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S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: Unknown

Serial No.: Unknown

Group Art Unit: Unknown

Filed: Herewith

Docket: 303.356US4

Title: OPERATING A MEMORY DEVICE

COMMUNICATION CONCERNING RELATED APPLICATION(S)

MS Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
08/903452	July 29, 1997	303.324US1	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/256643	February 23, 1999	303.324US2	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/652420	August 31, 2000	303.324US3	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/691004	October 18, 2000	303.324US4	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
08/903486	July 29, 1997	303.326US1	SILICON CARBIDE GATE TRANSISTOR
09/259870	March 1, 1999	303.326US2	FABRICATION OF SILICON CARBIDE GATE TRANSISTOR
08/902132	July 29,	303.353US1	TRANSISTOR WITH SILICON

5886368	1997		OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
09/138294 6309907	August 21, 1998	303.353US2	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
08/902843	July 29, 1997	303.354US1	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/135413	August 14, 1998	303.354US2	METHOD FOR OPERATING A MEMORY DEVICE HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/134713	August 14, 1998	303.354US3	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
08/902098 6031263	July 29, 1997	303.355US1	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/140978 6307775	August 27, 1998	303.355US2	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/141392 6249020	August 27, 1998	303.355US3	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/883795	June 18, 2001	303.355US4	METHOD OF FORMING A DEVICE WITH A GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
10/047181	October 23, 2001	303.355US5	MEMORY DEVICE WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
08/902133	July 29, 1997	303.356US1	MEMORY DEVICE
10/231687	August 29,	303.356US2	DYNAMIC ELECTRICALLY

	2002		ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE
08/903453	July 29, 1997	303.378US1	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
09/258467	February 26, 1999	303.378US2	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
09/650553	August 30, 2000	303.378US3	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
10/461593	June 11, 2003	303.356US3	MEMORY DEVICE

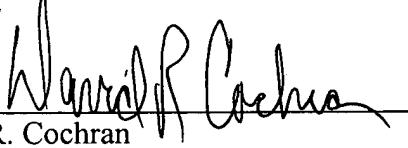
Respectfully submitted,

LEONARD FORBES ET AL.

By Applicants' Representatives,

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Date 27 February 2004 By _____


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